IN THE CLAIMS:

1. (Cancelled)

2. (Previously Presented) A display device, comprising:

a display element;

a control element for controlling a voltage or a current to be applied to said display element to drive said display element; and

a nonvolatile data holding section integrated with said control element or connected to said control element and capable of holding control data of said control element in a floating state;

wherein said control element is formed of a MOS transistor type element, one of a drain and a source of said MOS transistor type element is connected to said display element and the other is connected to a driving line, a gate side of said MOS transistor type element is connected to a control line through said nonvolatile data holding section, and plural sets of said display element, said control element and said nonvolatile data holding section are formed as each pixel in a matrix.

3. (Original) The display device of claim 2, wherein a selective transistor is connected between said nonvolatile data holding section and said control line, and a gate of said selective transistor is connected to a selective line.

4. (Previously Presented) The display device of claim 2, wherein said nonvolatile data holding section is formed of a ferroelectric capacitor.

5. (Original) The display device of claim 2, wherein said control element and said nonvolatile data holding section are formed of a transistor having an MFS structure or an MFIS structure in which a ferroelectric capacitor is formed integrally on the gate

side of a MOS transistor, a back gate of said MOS transistor is connected to a write line, and the control data can be written to said nonvolatile data holding section between said control line and said write line.

6. (Previously Presented) The display device of claim 2, wherein said control element and said nonvolatile data holding section are formed of a transistor having an MFMIS structure in which a ferroelectric capacitor is connected to the gate side of a MOS transistor through a common electrode or a wiring, a capacitor is connected between a connecting portion of a gate electrode of said MOS transistor with said ferroelectric capacitor and a ground or a write line, wherein the control data can be written to said nonvolatile data holding section by using said control line and said ground or said write line.

7. (Previously Presented) The display device of claim 2, wherein said nonvolatile data holding section is constituted by an element utilizing a magnetoresistance effect.

8. (Previously Presented) The display device of claim 2, wherein said nonvolatile data holding section is constituted by a single electron memory.

9. (Previously Presented) The display device of claim 2, wherein said display element is formed by an organic EL element.

10. (Cancelled)

11. (Currently Amended) The display device of claim 2, wherein said control element is formed of a MOS transistor, said nonvolatile data holding section is formed of a ferroelectric capacitor which is connected to a gate of said MOS transistor type element, and a capacitor is connected between a connecting portion of said gate

with said ferroelectric capacitor and a ground or a write line, wherein the control data is written to said nonvolatile data holding section by using said control line and said ground or said write line.